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I Roger P. Lewis, whose address is 42 Bird Street North, Martinsburg WV 25401, declare and state the following:

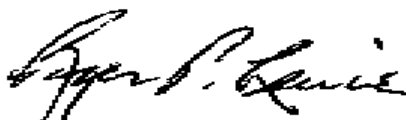
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is true, and that all statements of information and belief are believed to be true, and that these and similar statements are punishable by fines or imprisonment, or both, under Section 1001 of Title 18 of the United States Code.

SINCERELY,

A handwritten signature in black ink, appearing to read "Roger P. Lewis". The signature is written in a cursive style with some loops and flourishes.

ROGER P. LEWIS

Date: June 10, 2016

[Document Name] Patent Application
[Docket Number] 2020270244
[Submission Date] December 19, 1995
[Submitted to] Commissioner of Japan Patent Office
[International Patent Classification] H01L 21/76
[Title of the Invention] SEMICONDUCTOR DEVICE AND MANUFACTURING
METHOD THEREOF
[Number of claims] 12
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[Indication of Fees]

[Payment Method] Deposit

[Deposit Account Number] 014409

[Amount deposited] 21,000 JPY

[List of Submitted Items]

[Item Name] Specification 1

[Item Name] Drawings 1

[Item Name] Abstract 1

[General Power of Attorney Number] 9006026

[Necessity of Proof] Necessary

[Document Name] Specification

[Title of the Invention] SEMICONDUCTOR DEVICE AND MANUFACTURING
METHOD THEREOF

[Claims]

1. A semiconductor device, comprising:
 - a semiconductor substrate,
 - an element formation region placed in a portion of the substrate,
 - groove-type element isolation that surrounds the element formation region, and that comprises a height difference part, which becomes higher in a step manner than the semiconductor substrate of the element formation region, with the element formation region, and that is made from an insulating material, and
 - height difference-part sidewalls formed on side surfaces of the height difference part between the element formation region and the groove-type element isolation.
2. The semiconductor device according to claim 1, wherein
 - the height difference-part sidewalls are formed with an insulating material.
3. The semiconductor device according to claim 1, wherein
 - a MISFET, comprising: a gate electrode and electrode-part sidewalls on both side surfaces of the gate electrode is formed in the element formation region, and
 - the height difference-part sidewalls are formed at the same time as the electrode-part sidewalls.
4. The substrate device according to claim 3,
 - the electrode-part sidewalls are formed with an L-shaped silicon nitride film with substantially constant thickness that is formed via a protective oxide film throughout the side surfaces of the gate electrode onto the semiconductor substrate; and
 - the height difference-part sidewalls are formed with an L-shaped silicon nitride film with substantially constant thickness that are formed via a protective oxide film throughout side surfaces between the element formation region and the groove-type element isolation onto the semiconductor substrate.

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